

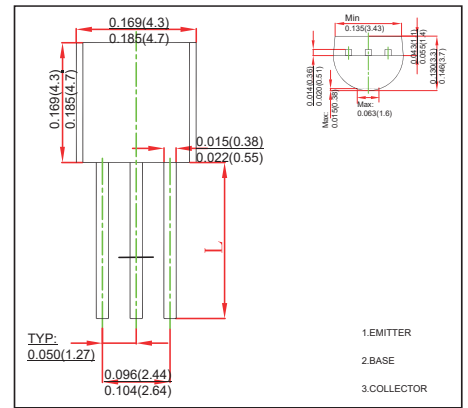
TO-92 Plastic-Encapsulate Transistors

FEATURES

- High DC Current Gain
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.8	A
Collector Power Dissipation	P_D	625	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	200	°C /W
Operation Junction and Storage Temperature Range	T_j, T_{stg}	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.5mA, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.05mA, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -100mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -20mA$			-0.5	V
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		19		pF
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$		120		MHz